

MICROWAVE POWER GaAs FET

TIM7179-4UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 36.5dBm at 7.1GHz to 7.9GHz

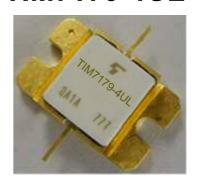
·HIGH GAIN

G1dB= 9.0dB at 7.1GHz to 7.9GHz

LOW INTERMODULATION DISTORTION

IM3(MIN.) = -44dBc at Pout= 25.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 0.9A f= 7.1 to 7.9GHz Two-Tone Test Po= 25.5dBm, Δf= 5MHz (Single Carrier Level)	dBm	35.5	36.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0	
Drain Current	IDS1		Α	_	1.1	1.3
Gain Flatness	ΔG		dB	_	_	±0.6
Power Added Efficiency	ηadd		%	_	35	_
3rd Order Intermodulation Distortion	IM3		dBc	-44	-47	
Drain Current	IDS2		Α	_	1.1	1.3
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_		80

Recommended Gate Resistance(Rg): 150 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 1.5A	S	_	0.9	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 15mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	2.6	_
Gate-Source Breakdown Voltage	VGSO	IGS= -50μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	4.5	6.0

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

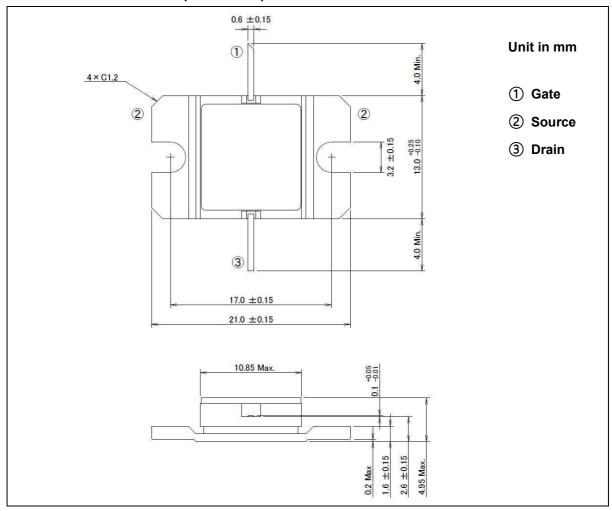
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	3.5
Total Power Dissipation (Tc= 25°C)	PT	W	25
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11D1B)



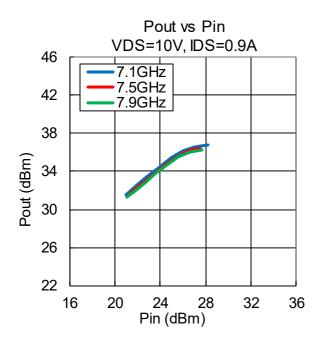
HANDLING PRECAUTIONS FOR PACKAGE MODEL

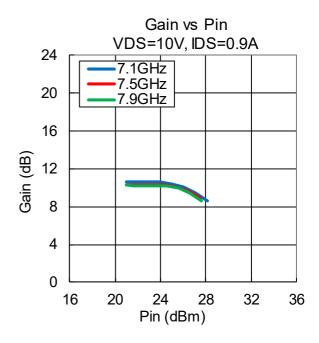
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

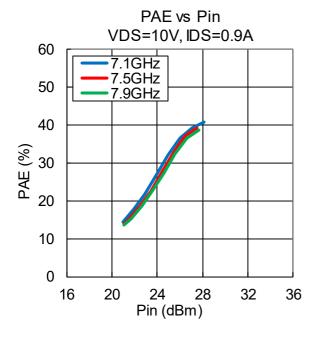
TYPICAL RF PERFORMANCE

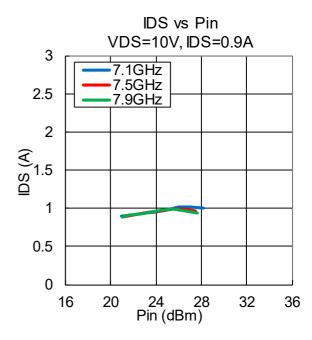
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 0.9 A, f= 7.1, 7.5, 7.9 GHz, Ta= +25 °C



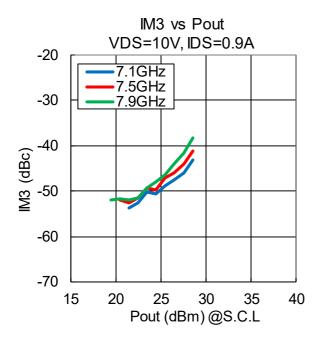


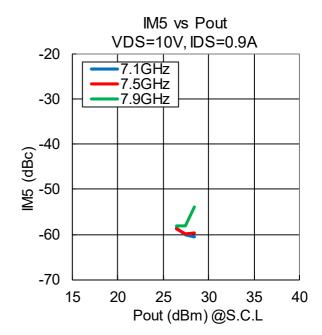




·IM3, IM5 vs. Pout

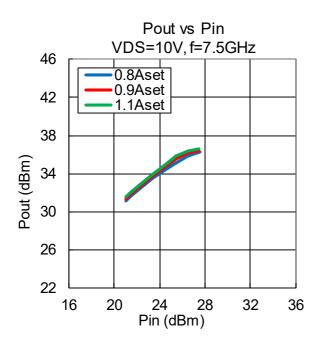
VDS= 10 V, IDSset= 0.9 A, f= 7.1, 7.5, 7.9 GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C

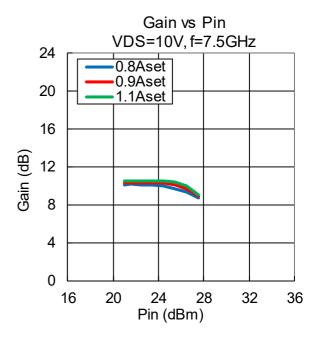


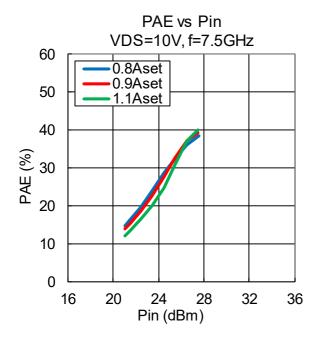


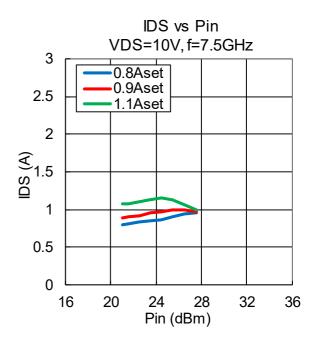
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 0.8, 0.9, 1.1 A, f= 7.5 GHz, Ta= +25 $^{\circ}$ C



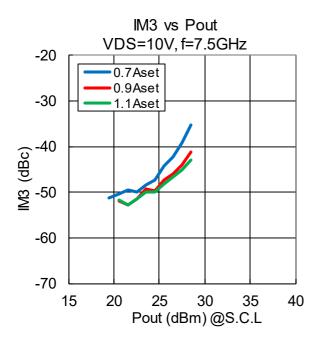


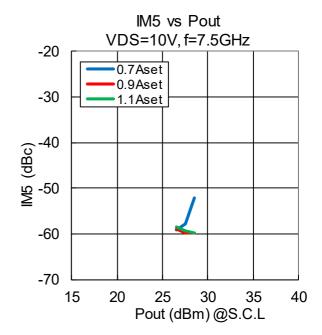




·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 0.7, 0.9, 1.1 A, f= 7.5 GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C

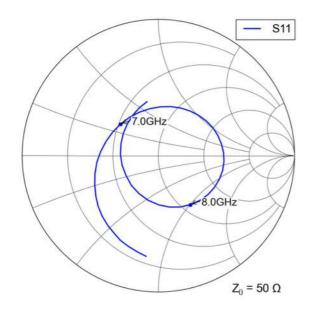


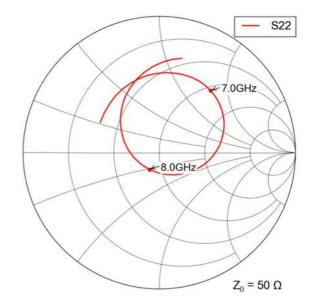


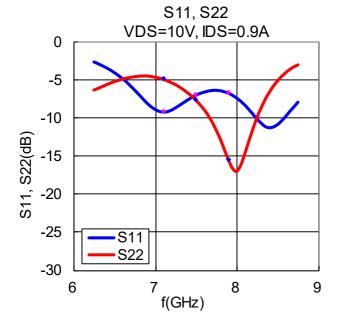


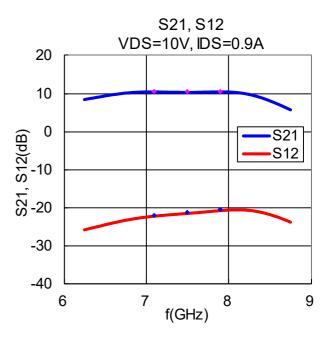
·S-Parameters

VDS= 10 V, IDSset= 0.9 A, f= 6.25 to 8.75 GHz, Ta= +25 $^{\circ}$ C











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